

ABSTRACT OF THE DISCLOSURE

METHOD FOR FORMING SELF-ALIGNED CONTACTS/ VIAS WITH HIGH CORNER SELECTIVITY

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A method of etching self-aligned contact/via features in a low-k dielectric layer disposed below a hardmask, which is disposed below a planarization layer. At least one cycle is provided, where each cycle comprises thinning the planarization layer; forming a deposition layer on the hardmask and planarization layer; and etching the low-k dielectric layer masked by the deposition layer.

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FIG. 1

